

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ($L^2\text{-}\pi\text{-MOSV}$)**2SJ620**

Switching Regulator and DC-DC Converter Applications

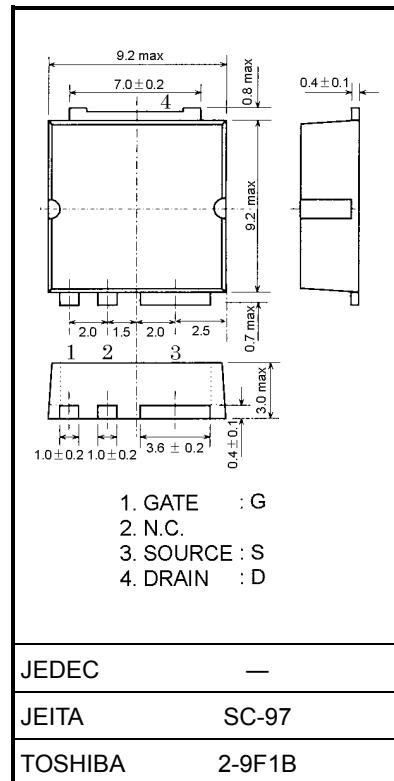
Motor Drive Applications

Unit: mm

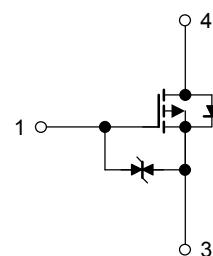
- 4-V gate drive
- Low drain-source ON resistance: $R_{DS(\text{ON})} = 63 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 15 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -100 \mu\text{A}$ (max) ($V_{DS} = -100 \text{ V}$)
- Enhancement-model: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-100	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	-100	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current DC (Note 1)	I_D	-18	A
	I_{DP}	-72	
Drain power dissipation ($T_c = 25^\circ\text{C}$)	P_D	125	W
Single pulse avalanche energy (Note 2)	E_{AS}	937	mJ
Avalanche current	I_{AR}	-18	A
Repetitive avalanche energy (Note 3)	E_{AR}	12.5	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$



Weight: 0.74 g (typ.)

Circuit Configuration**Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th} (\text{ch-c})$	1.0	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

Note 2: $V_{DD} = -50 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 3.56 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = -18 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

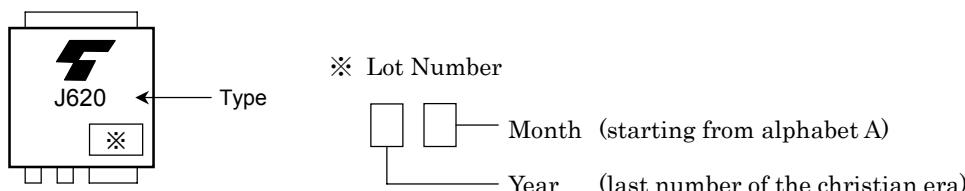
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

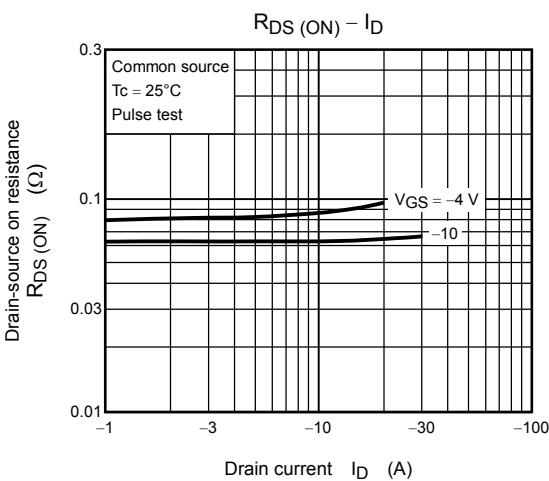
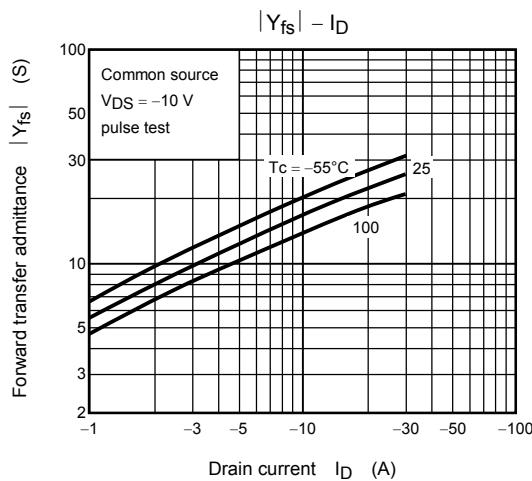
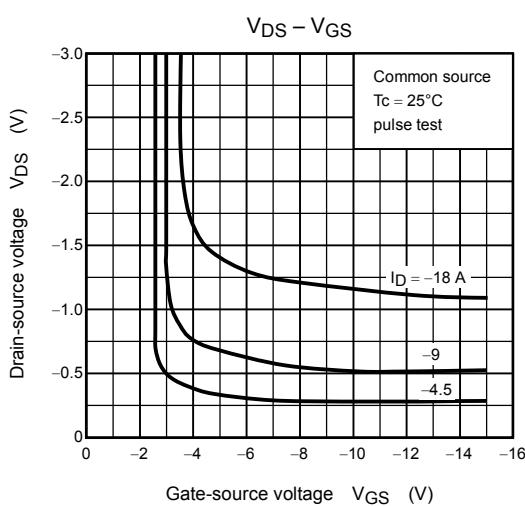
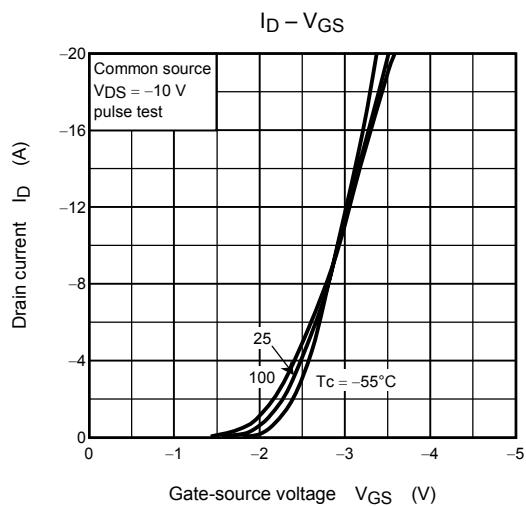
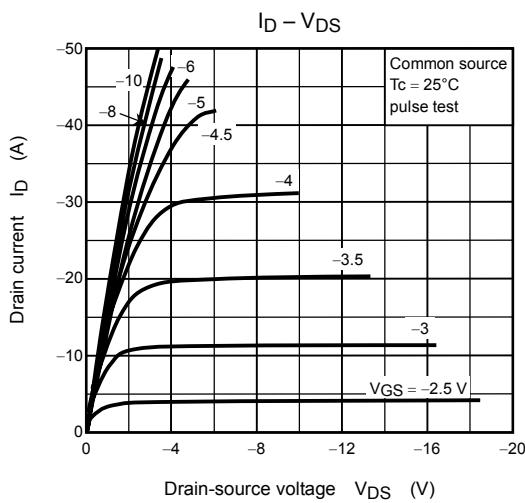
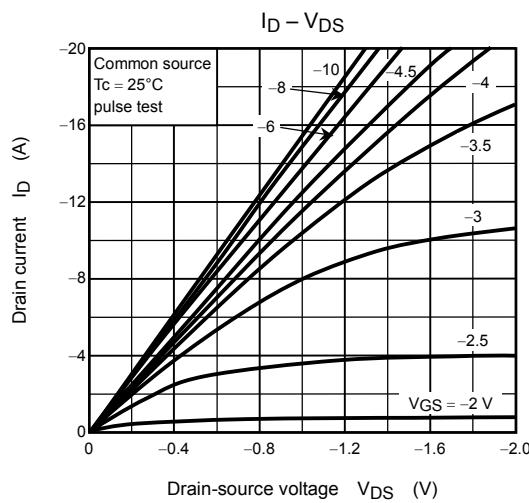
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA	
Drain cut-OFF current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$	—	—	-100	μA	
Drain-source breakdown voltage	$V_{(BR) DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-100	—	—	V	
Gate threshold voltage	V_{th}	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V	
Drain-source ON resistance	$R_{DS (\text{ON})}$	$V_{GS} = -4\text{ V}, I_D = -9\text{ A}$	—	85	120	$\text{m}\Omega$	
		$V_{GS} = -10\text{ V}, I_D = -9\text{ A}$	—	63	90		
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -6\text{ A}$	7	15	—	S	
Input capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2900	—	pF	
Reverse transfer capacitance	C_{rss}		—	480	—		
Output capacitance	C_{oss}		—	1000	—		
Switching time	Rise time	t_r	 V_{GS} 0 V -10 V $I_D = -9\text{ A}$ V_{OUT} C_L $4.7\text{ }\mu\text{F}$ $R_L = 5.5\Omega$ $V_{DD} \approx -50\text{ V}$ Duty $\leq 1\%$, $t_W = 10\text{ }\mu\text{s}$	—	25	—	ns
	Turn-ON time	t_{on}		—	45	—	
	Fall time	t_f		—	25	—	
	Turn-OFF time	t_{off}		—	170	—	
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -80\text{ V}, V_{GS} = -10\text{ V}, I_D = -18\text{ A}$	—	140	—	nC	
Gate-source charge	Q_{gs}		—	90	—		
Gate-drain ("miller") charge	Q_{gd}		—	50	—		

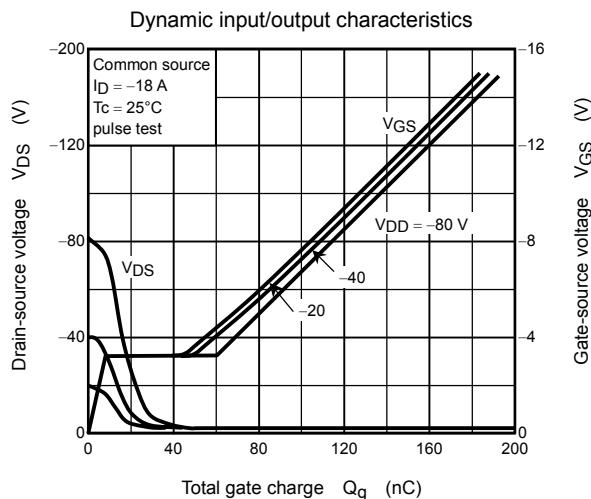
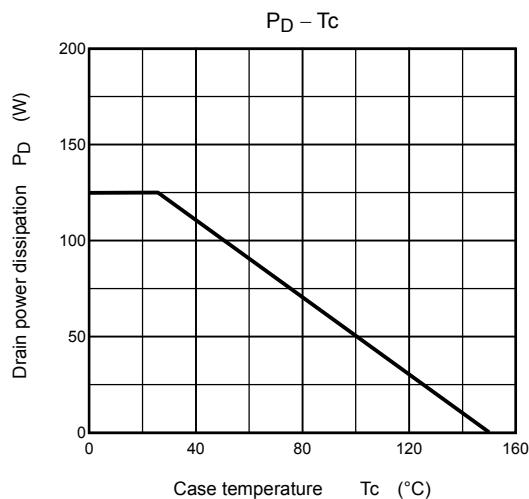
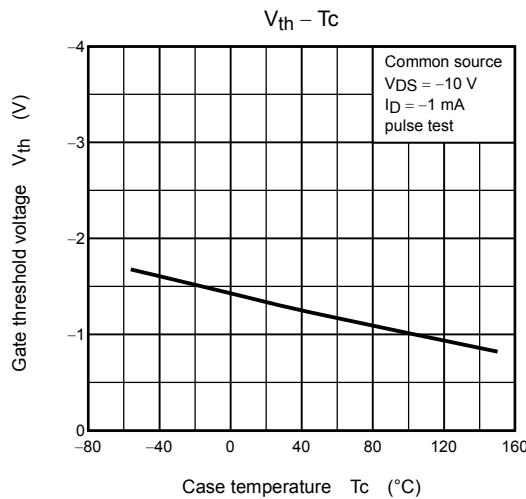
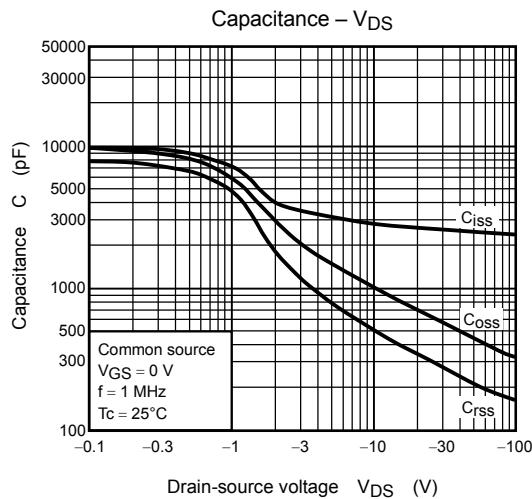
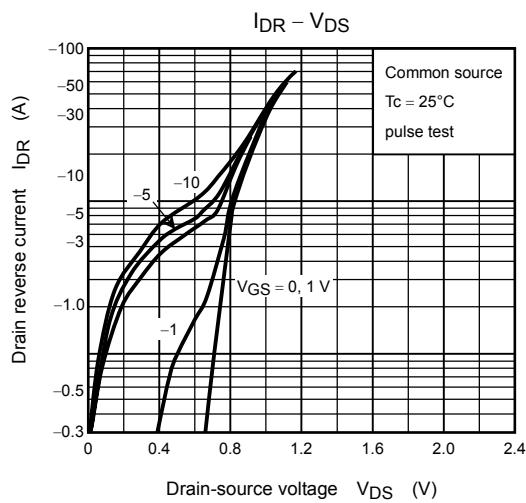
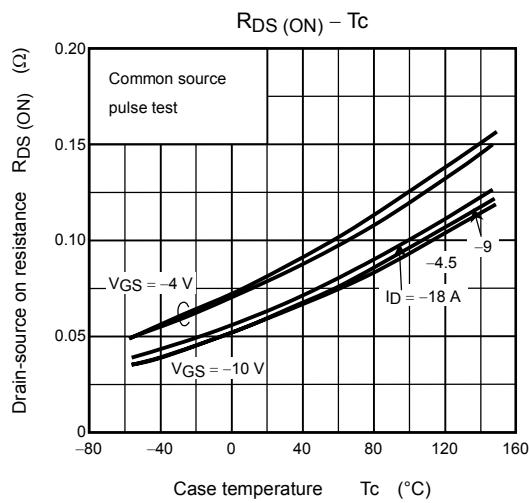
Source-Drain Ratings and Characteristics ($T_a = 25^\circ\text{C}$)

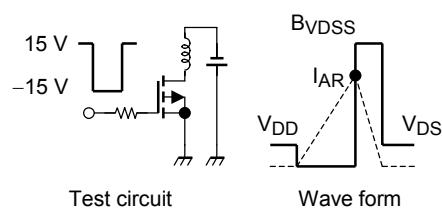
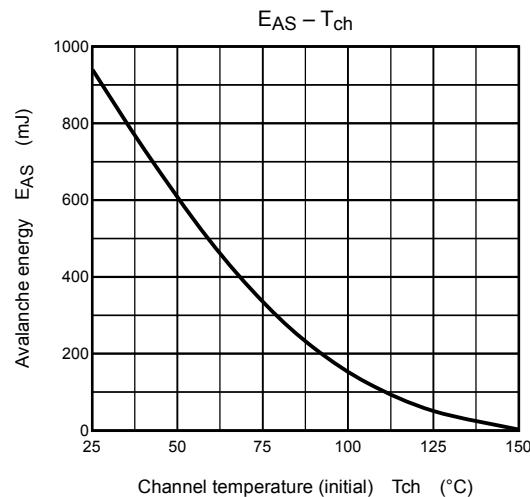
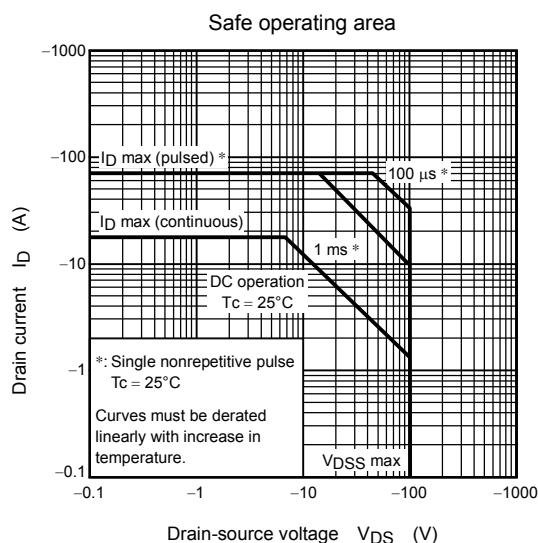
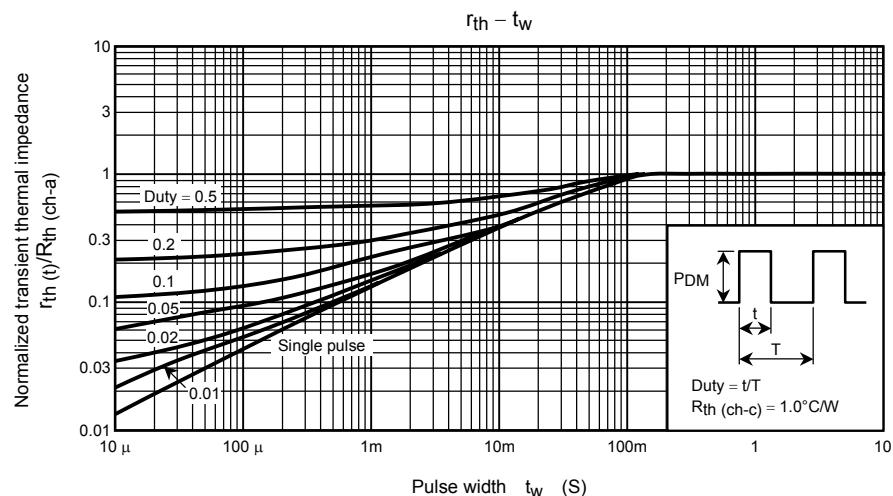
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	-18	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	-72	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = -18\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = -18\text{ A}, V_{GS} = 0\text{ V},$ $dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	220	—	μs
Reverse recovery charge	Q_{rr}		—	0.97	—	μC

Marking









$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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